STB27NM60ND, STW27NM60ND

Automotive-grade N-channel 600 V, 0.13 Ω, 21 A FDmesh™ II Power MOSFETs (with fast diode) in D²PAK and TO-247 packages

Datasheet - production data

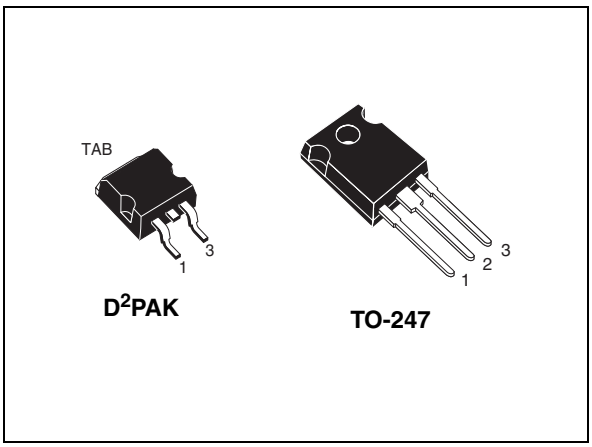
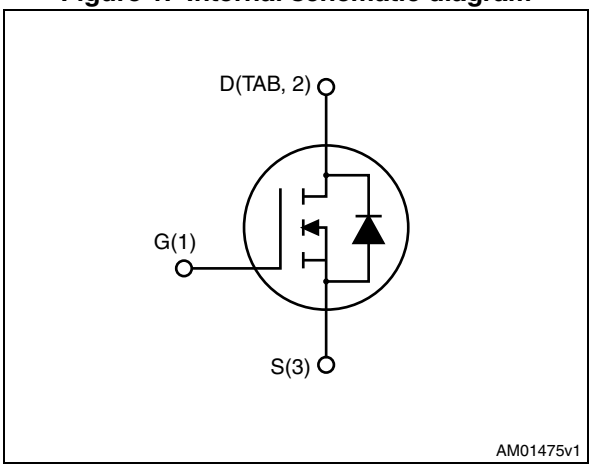


Figure 1. Internal schematic diagram



Features

Order codes	V_{DS} @ T_{jmax}	$R_{DS(on)}$ max	I_D
STB27NM60ND	650 V	0.16 Ω	21 A
STW27NM60ND			

- Designed for automotive applications and AEC-Q101 qualified
- The worldwide best $R_{DS(on)}$*area amongst the fast recovery diode devices
- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance
- Extremely high dv/dt and avalanche capabilities

Applications

- Switching applications

Description

These FDmesh™ II Power MOSFETs with intrinsic fast-recovery body diode are produced using the second generation of MDmesh™ technology. Utilizing a new strip-layout vertical structure, these revolutionary devices feature extremely low on-resistance and superior switching performance. They are ideal for bridge topologies and ZVS phase-shift converters.

Table 1. Device summary

Order codes	Marking	Packages	Packaging
STB27NM60ND	27NM60ND	D²PAK	Tape and reel
STW27NM60ND	27NM60ND	TO-247	Tube

Contents

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	600	V
V_{GS}	Gate-source voltage	±25	V
I_D	Drain current (continuous) at T_C = 25 °C	21	A
I_D	Drain current (continuous) at T_C = 100 °C	13	A
I_{DM} (1)	Drain current (pulsed)	84	A
P_{TOT}	Total dissipation at T_C = 25 °C	160	W
dv/dt(2)	Peak diode recovery voltage slope	40	V/ns
T_{stg}	Storage temperature	–55 to 150	°C
T_J	Max. operating junction temperature	150	°C

1. Pulse width limited by safe operating area
2. $I_{SD} \leq 21$ A, di/dt $\leq$ 600 A/µs, V_{DD} = 80% $V_{(BR)DSS}$

Table 3. Thermal data

Symbol	Parameter	D²PAK	TO-247	Unit
$R_{thj\text{-}case}$	Thermal resistance junction-case max	0.78		°C/W
$R_{thj\text{-}amb}$	Thermal resistance junction-ambient max		50	°C/W
$R_{thj\text{-}pcb}$ (1)	Thermal resistance junction-ambient max	30		°C/W

1. When mounted on 1inch² FR-4 board, 2 oz Cu

Table 4. Avalanche characteristics

Symbol	Parameter	Max value	Unit
I_{AS}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_J max)	10	A
E_{AS}	Single pulse avalanche energy (starting T_J = 25 °C, $I_D = I_{AS}$, V_{DD} = 50 V)	850	mJ

2 Electrical characteristics

(T_{CASE}=25 °C unless otherwise specified).

Table 5. On/off states

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
$V_{(BR)DSS}$	Drain-source breakdown voltage	I_D = 1 mA, V_{GS} = 0	600			V
dv/dt(1)	Drain source voltage slope	V_{DD}= 480 V, I_D= 21 A, V_{GS}= 10 V		48		V/ns
I_{DSS}	Zero gate voltage drain current (V_{GS} = 0)	V_{DS} = 600 V			1	µA
		V_{DS} = 600 V @T_C= 125 °C			100	µA
I_{GSS}	Gate-body leakage current (V_{DS} = 0)	V_{GS} = ± 20 V			±100	nA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250 µA	3	4	5	V
$R_{DS(on)}$	Static drain-source on- resistance	V_{GS} = 10 V, I_D = 10.5 A		0.13	0.16	Ω

1. Characteristic value at turn off on inductive load.

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward transconductance	V_{DS} = 15 V, I_D = 10.5 A	-	17	-	S
C_{iss}	Input capacitance	V_{DS} = 50 V, f = 1 MHz, V_{GS} = 0	-	2400	-	pF
C_{oss}	Output capacitance		-	150	-	pF
C_{rss}	Reverse transfer capacitance		-	15	-	pF
$C_{oss\ eq.}$ (2)	Equivalent output capacitance	V_{GS} = 0, V_{DS} = 0 to 480 V	-	320	-	pF
$t_{d(on)}$	Turn-on delay time	V_{DD} = 300 V, I_D = 10.5 A R_G = 4.7 Ω V_{GS} = 10 V *(see Figure 21)*, *(see Figure 16)*	-	60	-	ns
t_r	Rise time		-	30	-	ns
$t_{d(off)}$	Turn-off delay time		-	50	-	ns
t_f	Fall time		-	40	-	ns

Table 6. Dynamic (continued)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
Q_g	Total gate charge	V_{DD} = 480 V, I_D = 21 A, V_{GS} = 10 V, *(see Figure 17)*	-	80	-	nC
Q_{gs}	Gate-source charge		-	15	-	nC
Q_{gd}	Gate-drain charge		-	40	-	nC
R_g	Gate input resistance	f = 1 MHz, gate DC Bias = 0, test signal level = 20 mV, I_D = 0	-	1.6	-	Ω

1. Pulsed: pulse duration=300µs, duty cycle 1.5%
2. $C_{oss\ eq}$. is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		21	A
I_{SDM} (1)	Source-drain current (pulsed)		-		84	A
V_{SD} (2)	Forward on voltage	I_{SD} = 21 A, V_{GS} = 0	-		1.3	V
t_{rr}	Reverse recovery time	I_{SD} = 21 A, V_{DD} = 60 V di/dt=100 A/µs *(see Figure 18)*	-	160		ns
Q_{rr}	Reverse recovery charge		-	1		µC
I_{RRM}	Reverse recovery current		-	15		A
t_{rr}	Reverse recovery time	I_{SD} = 21 A,V_{DD} = 60 V di/dt=100 A/µs, T_J = 150 °C *(see Figure 18)*	-	230		ns
Q_{rr}	Reverse recovery charge		-	2		µC
I_{RRM}	Reverse recovery current		-	19		A

1. Pulse width limited by safe operating area
2. Pulsed: Pulse duration = 300 µs, duty cycle 1.5%.

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for D²PAK

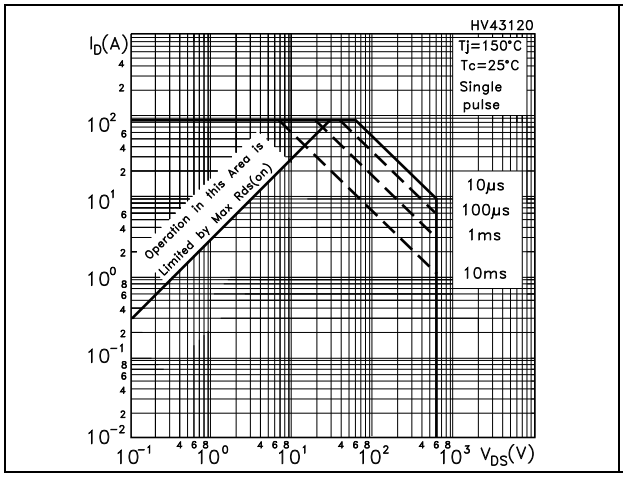


Figure 3. Thermal impedance for D²PAK

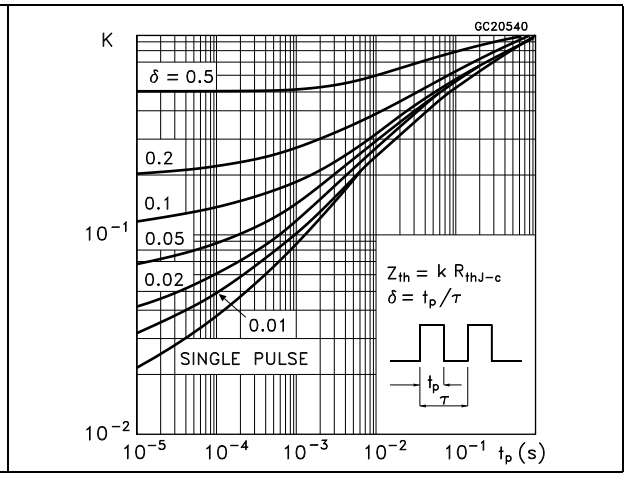


Figure 4. Safe operating area for TO-247

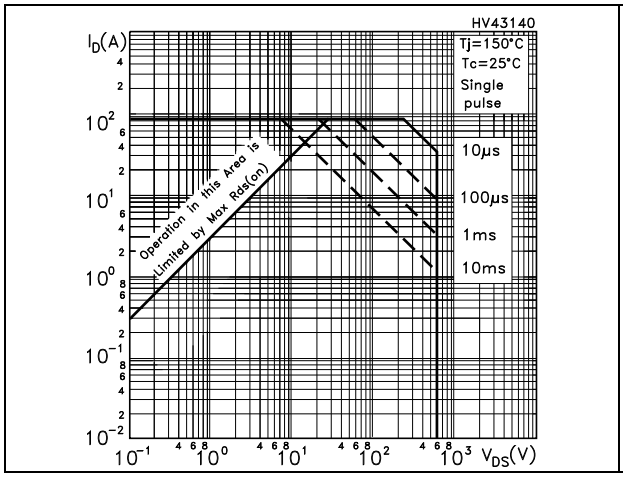


Figure 5. Thermal impedance for TO-247

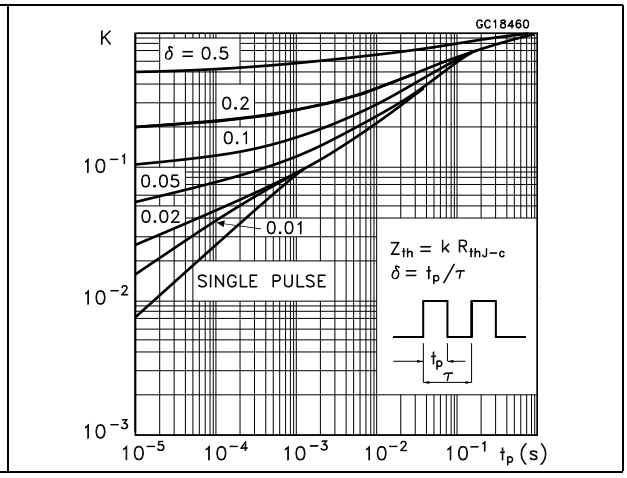


Figure 6. Output characteristics

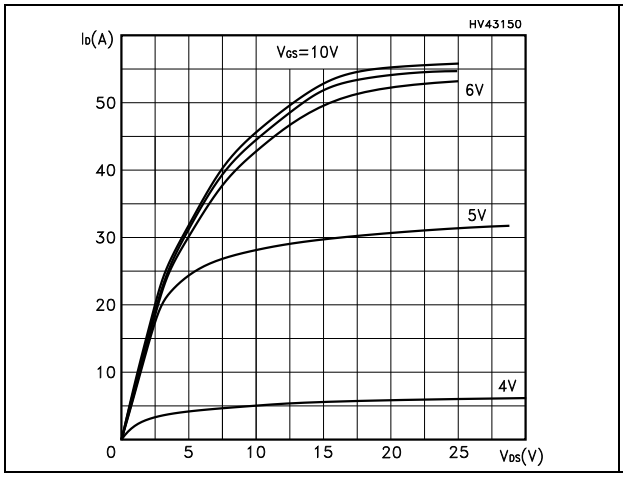


Figure 7. Transfer characteristics

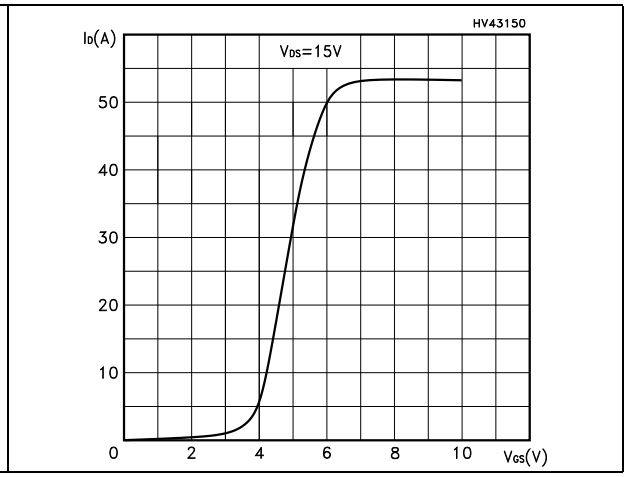


Figure 8. Transconductance

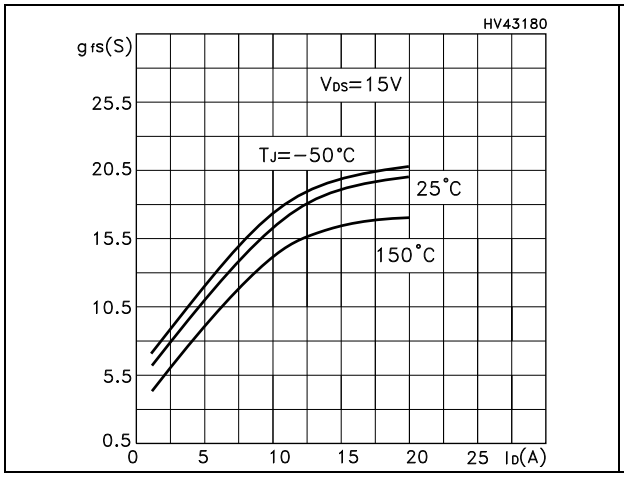


Figure 9. Static drain-source on-resistance

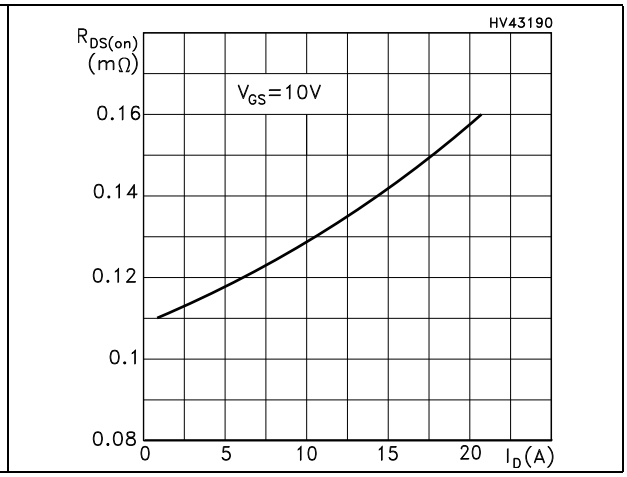


Figure 10. Gate charge vs gate-source voltage

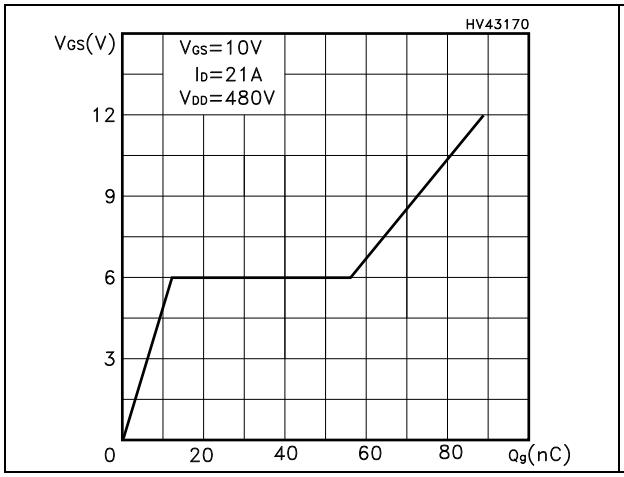


Figure 11. Capacitance variations

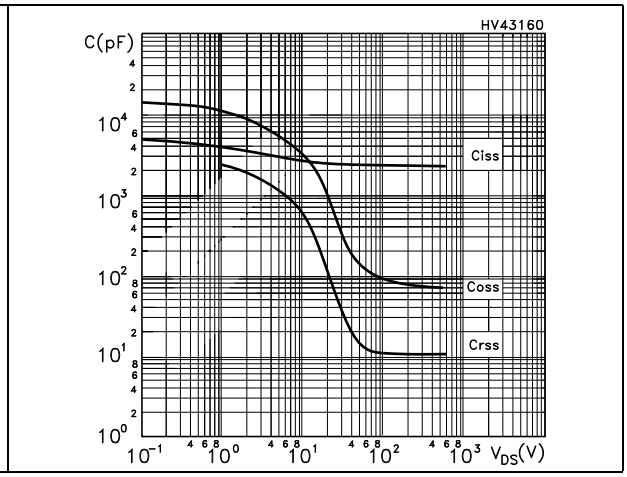


Figure 12. Normalized gate threshold voltage vs temperature

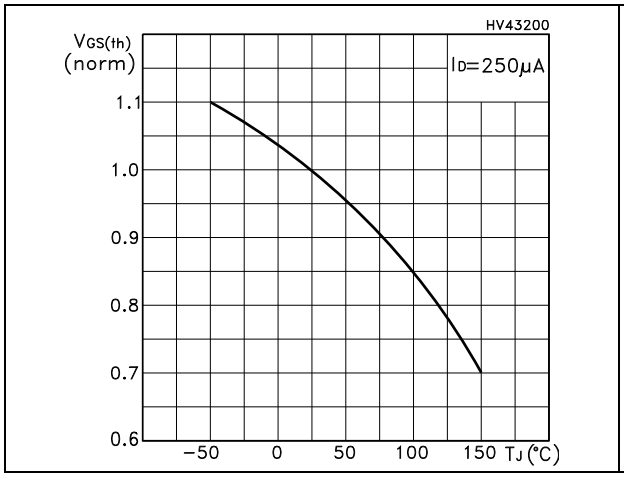


Figure 13. Normalized on-resistance vs temperature

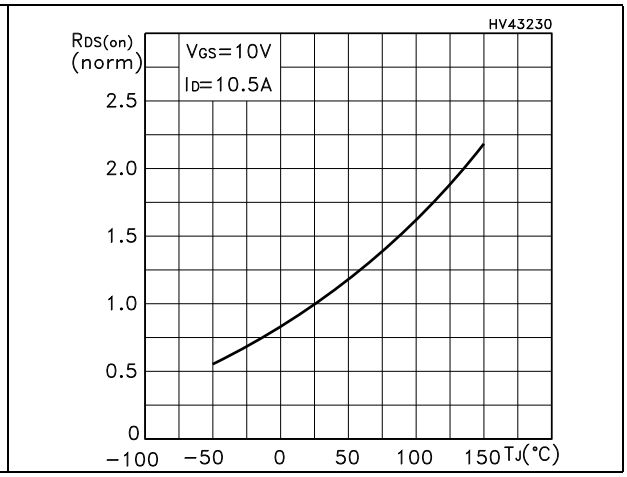


Figure 14. Source-drain diode forward characteristics

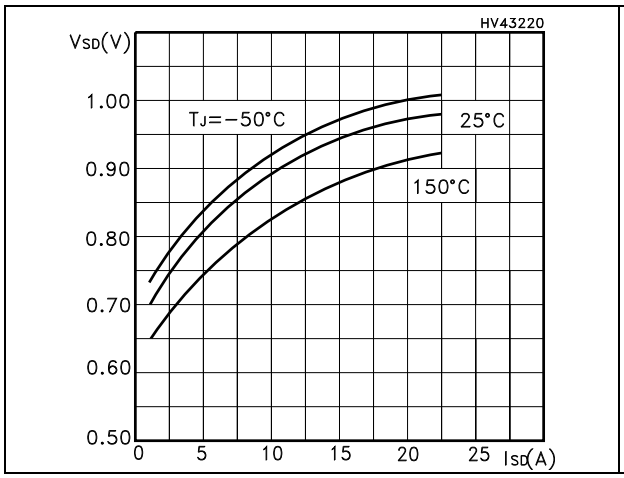
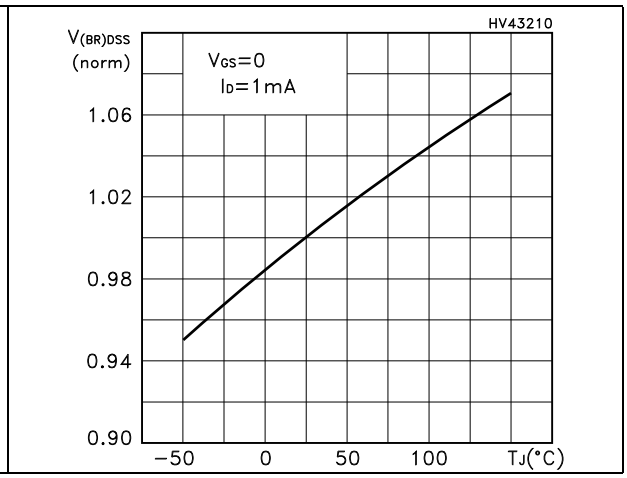


Figure 15. Normalized $V_{(BR)DSS}$ vs temperature



3 Test circuits

Figure 16. Switching times test circuit for resistive load

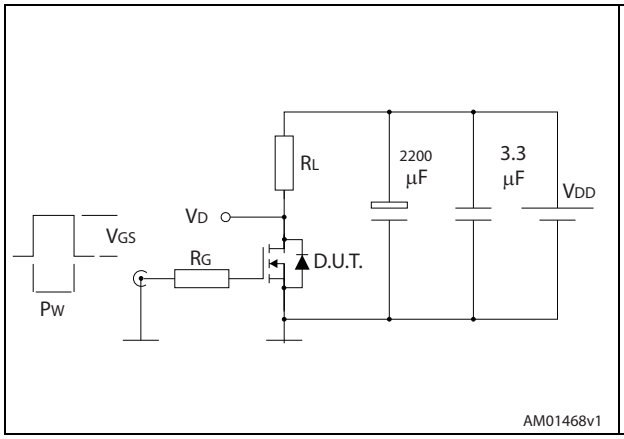


Figure 17. Gate charge test circuit

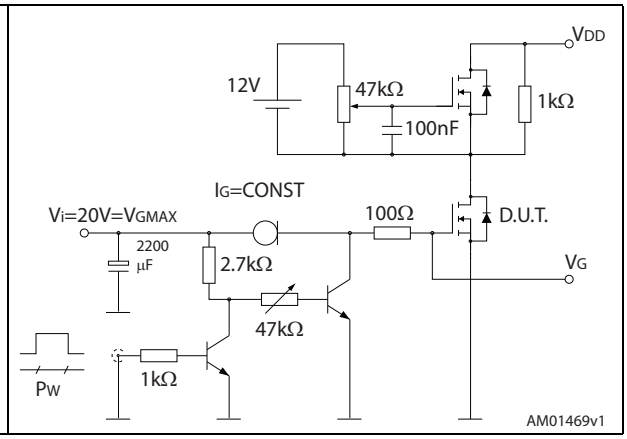


Figure 18. Test circuit for inductive load switching and diode recovery times

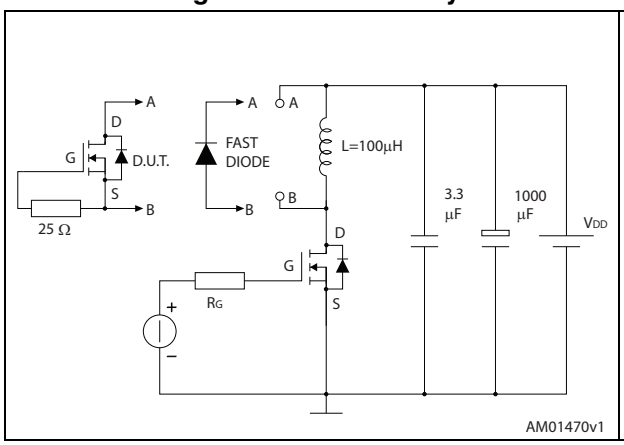


Figure 19. Unclamped inductive load test circuit

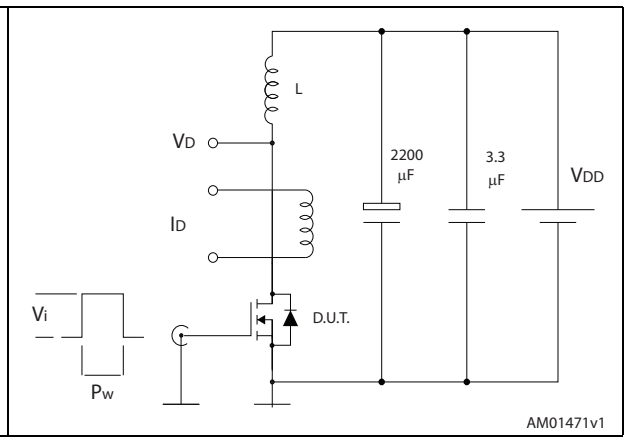


Figure 20. Unclamped inductive waveform

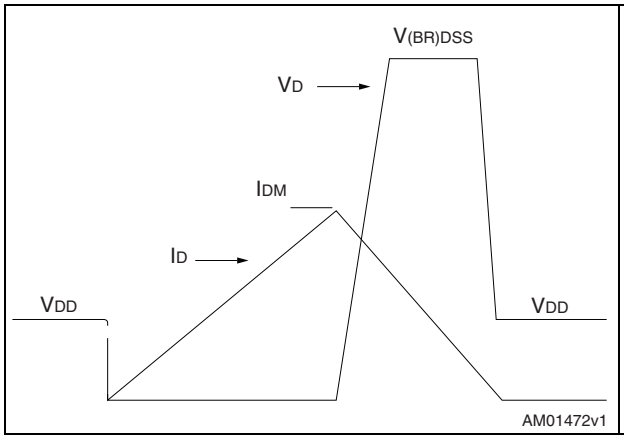
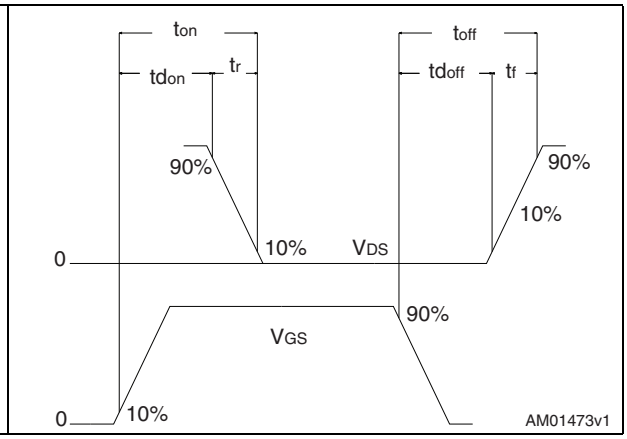


Figure 21. Switching time waveform



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: *www.st.com*.
ECOPACK® is an ST trademark.

Table 8. D²PAK (TO-263) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50		
E	10		10.40
E1	8.50		
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

Figure 22. D²PAK (TO-263) drawing

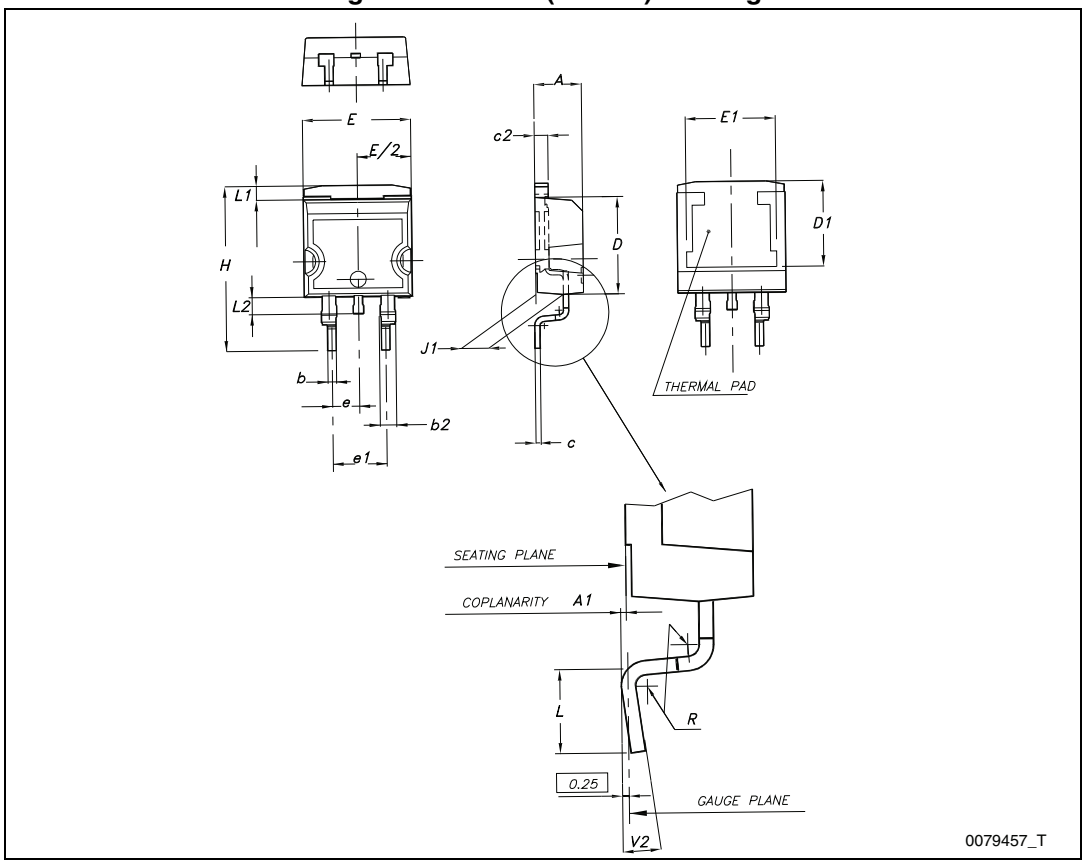
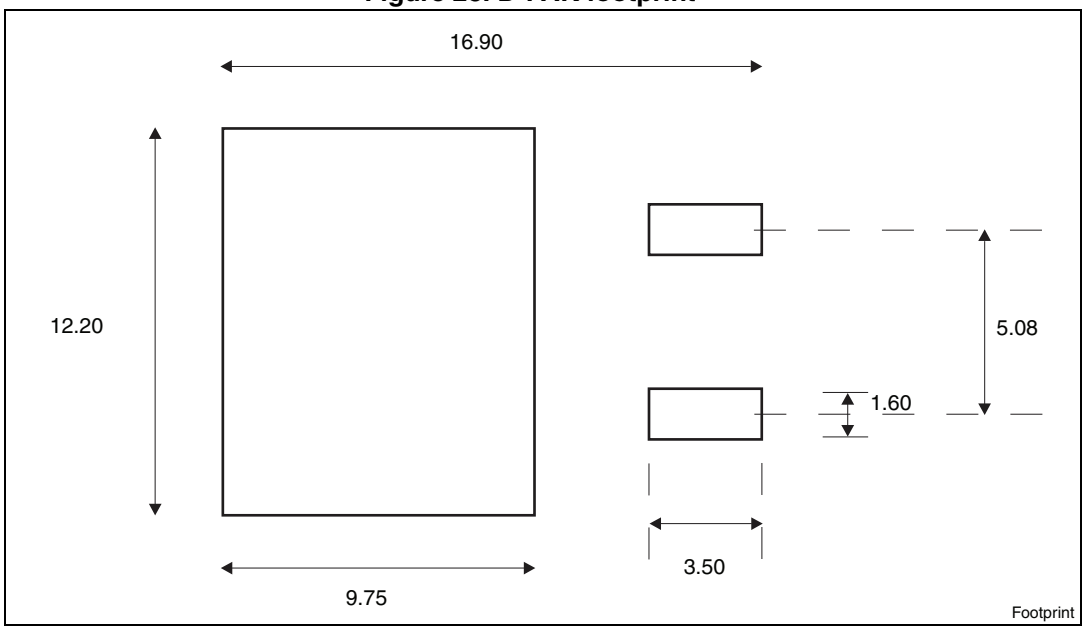


Figure 23. D²PAK footprint[a]

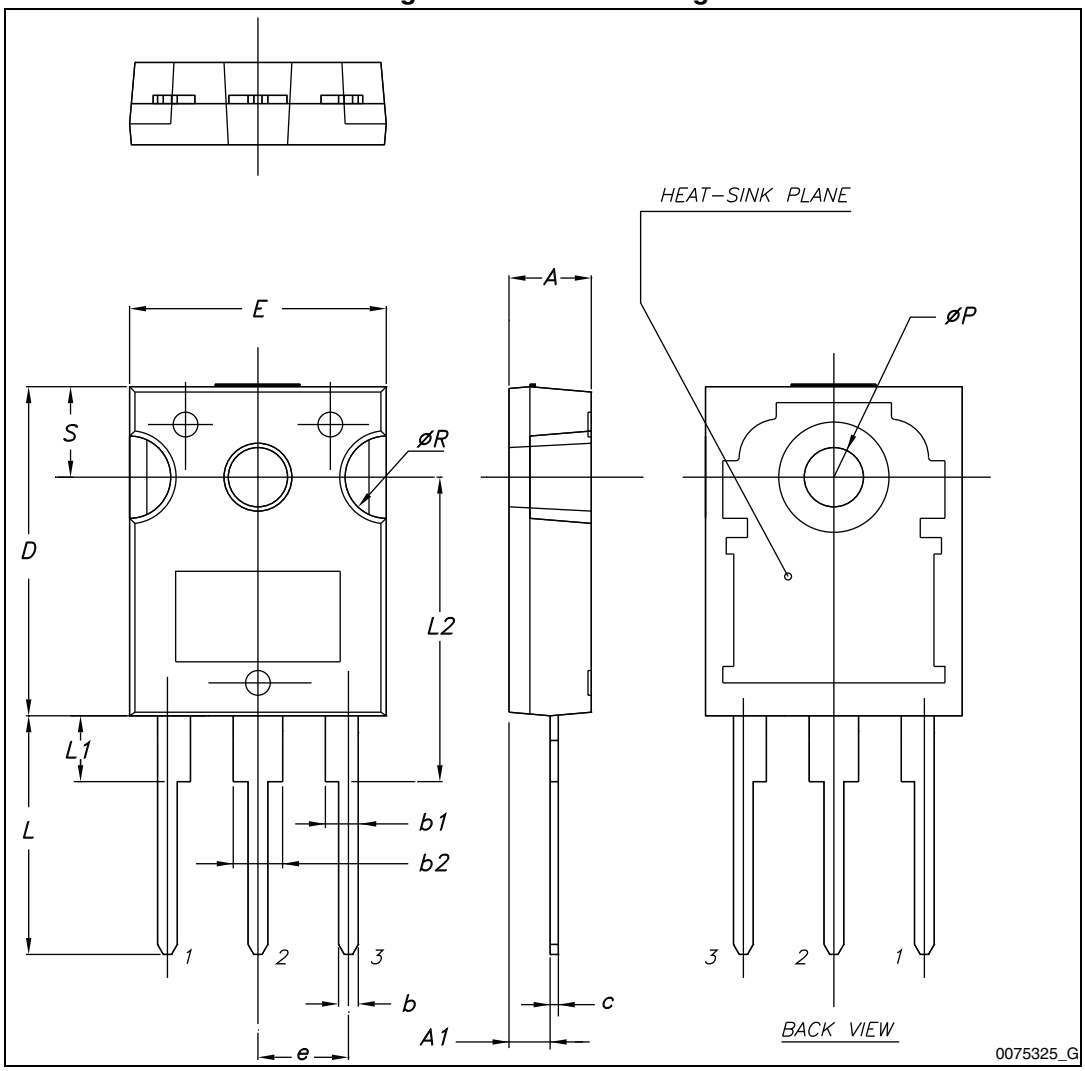


a. All dimension are in millimeters

Table 9. TO-247 mechanical data

Dim.	mm.		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e	5.30	5.45	5.60
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
∅P	3.55		3.65
∅R	4.50		5.50
S	5.30	5.50	5.70

Figure 24. TO-247 drawing



5 Packing mechanical data

Table 10. D²PAK (TO-263) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base qty		1000
P2	1.9	2.1	Bulk qty		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

Figure 25. Tape

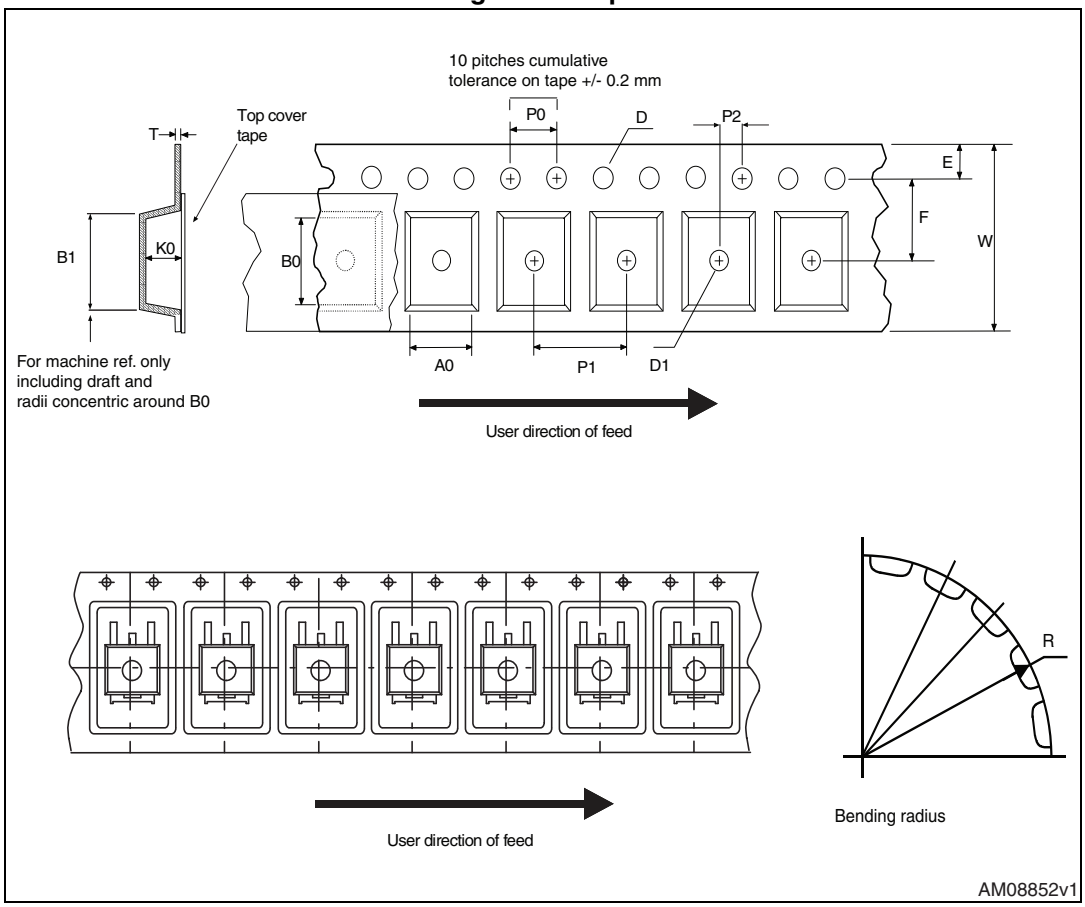
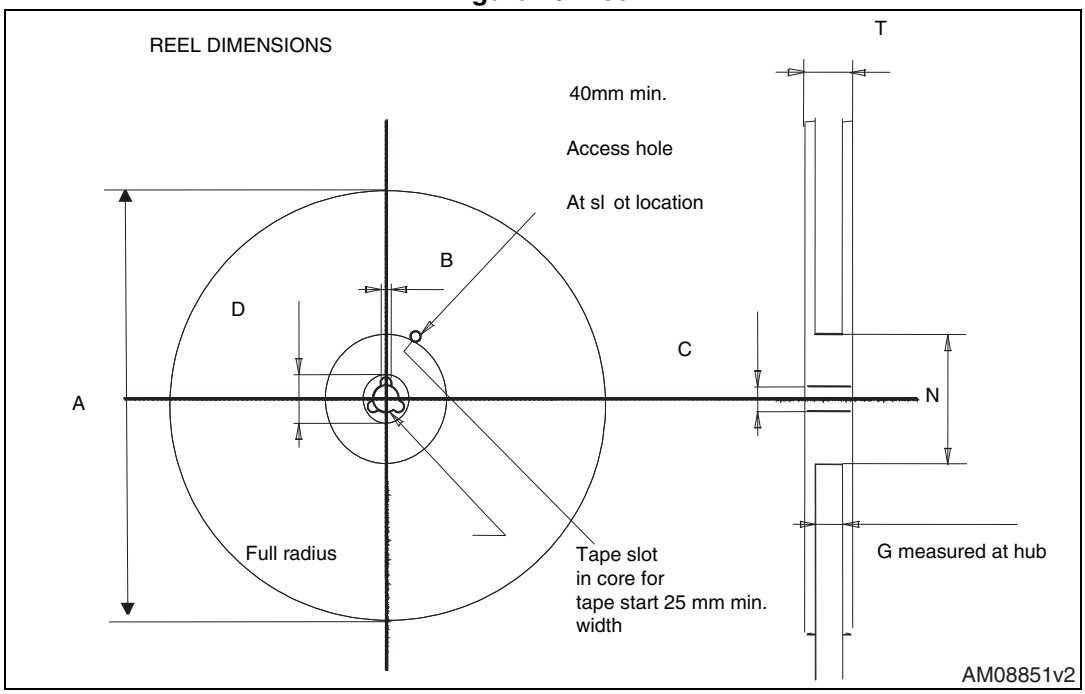


Figure 26. Reel



6 Revision history

Table 11. Document revision history

Date	Revision	Changes
02-Mar-2009	1	First release.
08-Mar-2011	2	Document status promoted from preliminary data to datasheet.
28-Nov-2011	3	Inserted new device in D^2PAK. Updated *Table 1: Device summary*, *Table 3: Thermal data*, *Section 3: Test circuits* and *Section 4: Package mechanical data* Inserted *Section 5: Packing mechanical data*. – Minor text changes.
31-Oct-2013	4	– Updated: title and features in cover page – Updated: *Section 4: Package mechanical data* and *Section 5: Packing mechanical data* – Minor text changes

Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries (“ST”) reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST’s terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST’S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

ST PRODUCTS ARE NOT DESIGNED OR AUTHORIZED FOR USE IN: (A) SAFETY CRITICAL APPLICATIONS SUCH AS LIFE SUPPORTING, ACTIVE IMPLANTED DEVICES OR SYSTEMS WITH PRODUCT FUNCTIONAL SAFETY REQUIREMENTS; (B) AERONAUTIC APPLICATIONS; (C) AUTOMOTIVE APPLICATIONS OR ENVIRONMENTS, AND/OR (D) AEROSPACE APPLICATIONS OR ENVIRONMENTS. WHERE ST PRODUCTS ARE NOT DESIGNED FOR SUCH USE, THE PURCHASER SHALL USE PRODUCTS AT PURCHASER’S SOLE RISK, EVEN IF ST HAS BEEN INFORMED IN WRITING OF SUCH USAGE, UNLESS A PRODUCT IS EXPRESSLY DESIGNATED BY ST AS BEING INTENDED FOR “AUTOMOTIVE, AUTOMOTIVE SAFETY OR MEDICAL” INDUSTRY DOMAINS ACCORDING TO ST PRODUCT DESIGN SPECIFICATIONS. PRODUCTS FORMALLY ESCC, QML OR JAN QUALIFIED ARE DEEMED SUITABLE FOR USE IN AEROSPACE BY THE CORRESPONDING GOVERNMENTAL AGENCY.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.
Information in this document supersedes and replaces all information previously supplied.
The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Philippines - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com

单击下面可查看定价，库存，交付和生命周期等信息

>>STMicro(意法半导体)